





### Replaces DS5804-4

Phase Control Thyristor

DS5804-5	August 2022	(LN41978)
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## **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

## **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages Vdrm and Vrrm (V)	Conditions
DCR2720V52* DCR2720V50 DCR2720V48	5200 5000 4800	$T_{vj} = -40^{\circ}C$ to 125°C, IDRM = IRRM = 200MA, VDRM, VRRM tp = 10ms VDSM & VRSM = VDRM & VRRM + 100V respectively

Lower voltage grades available.

\*5000V @ -40°C, 5200V @ 0°C

## **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

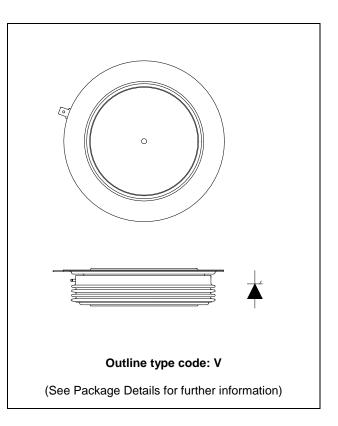
For example:

### DCR2720V52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS		
	5200V	
Ιτ(Αν)	2710A	
тѕм	36700A	
dV/dt*	1500V/µs	
dl/dt	300A/µs	

### \* Higher dV/dt selections are available on request





## **CURRENT RATINGS**

T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
Ιτ(Αν)	Mean on-state current	Half wave resistive load	2710	А
It(rms)	RMS value	-	4260	А
Гт	Continuous (direct) on-state current	-	4090	А

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## SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	36.7	kA
l²t	I <sup>2</sup> t for fusing	VR = 0	6.73	MA <sup>2</sup> s

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
	Rth(j-c) Thermal resistance - junction to case	Double side cooled	DC	-	7.5	°C/kW
Rth(j-c)			Anode DC	-	13.0	°C/kW
		Single side cooled	Cathode DC	-	17.8	°C/kW
Balan	Rth(c-h) Thermal resistance - case to heatsink	Clamping force 54kN	Double side	-	2.0	°C/kW
Ktn(c−n)		(with mounting compound)	Single side	-	4.0	°C/kW
Tvj	Virtual junction temperature	Blocking Vdrm / Vrrm		-	125	°C
Tstg	Storage temperature range	rature range		-55	125	°C
Fm	Clamping force			48	59	kN

# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Condition	IS	Min.	Max.	Units
Irrm/Idrm	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	200	mA
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		1.80	2.10	V
dV/dt	Max. linear rate of rise of off-state voltage	То 67% Vdrm, Тј = 125°С, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x $I_{T(AV)}$ Gate source 30V, 10 $\Omega$	Repetitive 50Hz	-	150	A/µs
avat		$tr < 0.5 \mu s, T_j = 125^{\circ}C$	Non-repetitive	-	300	A/µs
	Threshold voltage - Low level	500A to 2300A at Tcase = 125°C		-	0.91	V
<b>V</b> τ(το)	Threshold voltage - High level	2300A to 7000A at T <sub>case</sub> = 125°C		-	1.16	V
_	On-state slope resistance - low level	500A to 2300A at Tcase = 125°C		-	0.34	mΩ
ľτ	On-state slope resistance - High level	2300A to 7000A at T <sub>case</sub> = 125°C		-	0.23	mΩ
tgd	Delay time	V <sub>D</sub> = 67% V <sub>DRM</sub> , gate source 30V, 10Ω tr = 0.5μs, Tj = 25°C		-	3	μs
tq	Turn-off time	$T_{j} = 125^{\circ}C, V_{R} = 200V, dI/dt = 1A/\mu s,$ $dV_{DR}/dt = 20V/\mu s \text{ linear}$		-	600	μs
Qs	Stored charge	Iτ = 2000A, Tj = 125°C, dl/dt = 1A/μs		2050	4740	μC
Irr	Reverse recovery current	VR(peak) ~ 3100V, VRM ~ 2100V		37	58	А
lı.	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
Ін	Holding current	Tj = 25°C, R <sub>G-</sub> к = ∞, Iтм = 50	0A, I⊤ = 5A	-	300	mA

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## GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Vgт	Gate trigger voltage	Vdrм = 5V, Tcase = 25°С	1.5	V
Vgd	Gate non-trigger voltage	At 50% Vdrm, Tcase = 125°C	0.4	V
Іст	Gate trigger current	Vdrм = 5V, Tcase = 25°С	350	mA
Igd	Gate non-trigger current	At 50% Vdrм, Tcase = 125°C	15	mA

## **CURVES**

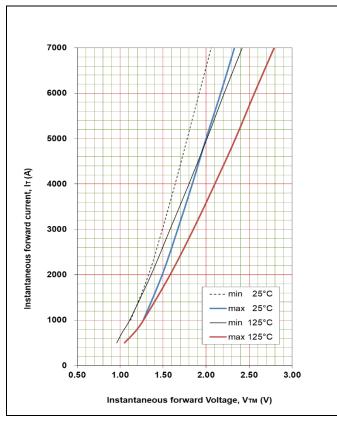


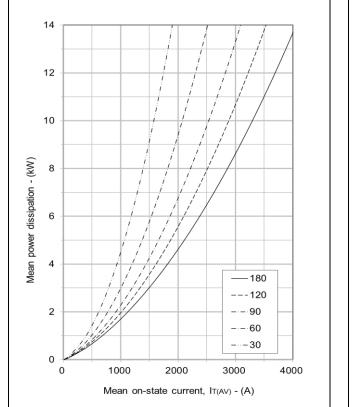
Fig. 2 Maximum & minimum on state characteristics

## **VTM EQUATION**

$$V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$$

Where A = -0.197621 B = 0.191438 C = 0.000209 D = -0.002006 These values are valid for  $T_j = 125^{\circ}C$  for IT 500A to 7000A

# DCR2720V52



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Fig. 3 On-state power dissipation - sine wave

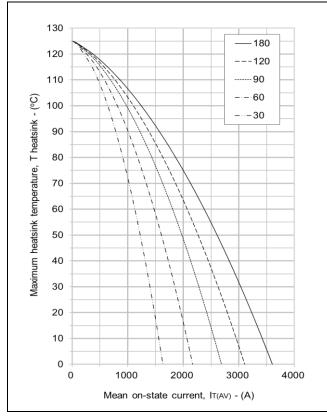


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

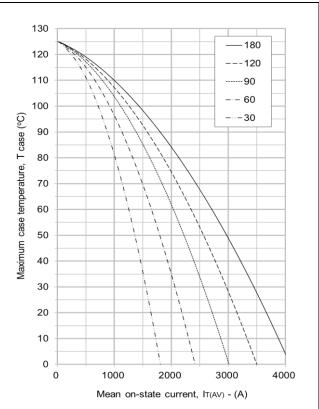


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

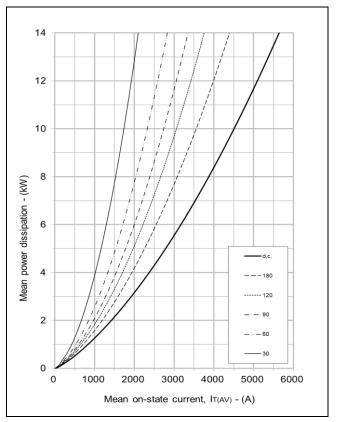


Fig. 6 On-state power dissipation - rectangular wave

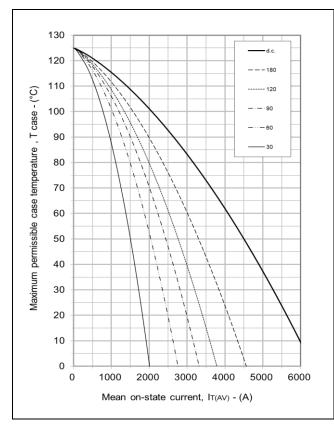
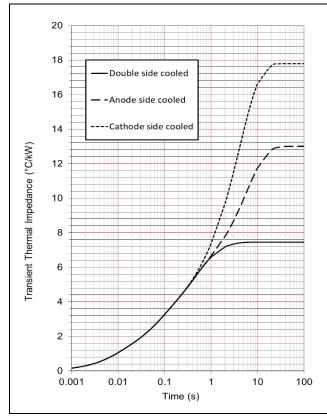


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



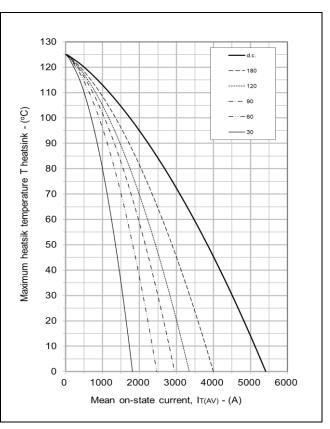


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	0.921	1.830	3.402	1.304
cooled	Ti(s)	0.008	0.058	0.408	1.209
Anode side cooled	Ri(°C/kW)	0.903	1.672	3.010	7.427
	Ti(s)	0.008	0.054	0.314	5.624
Cathode side	Ri(°C/kW)	0.948	2.066	1.688	13.085
cooled	Ti(s)	0.008	0.065	0.389	4.145

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

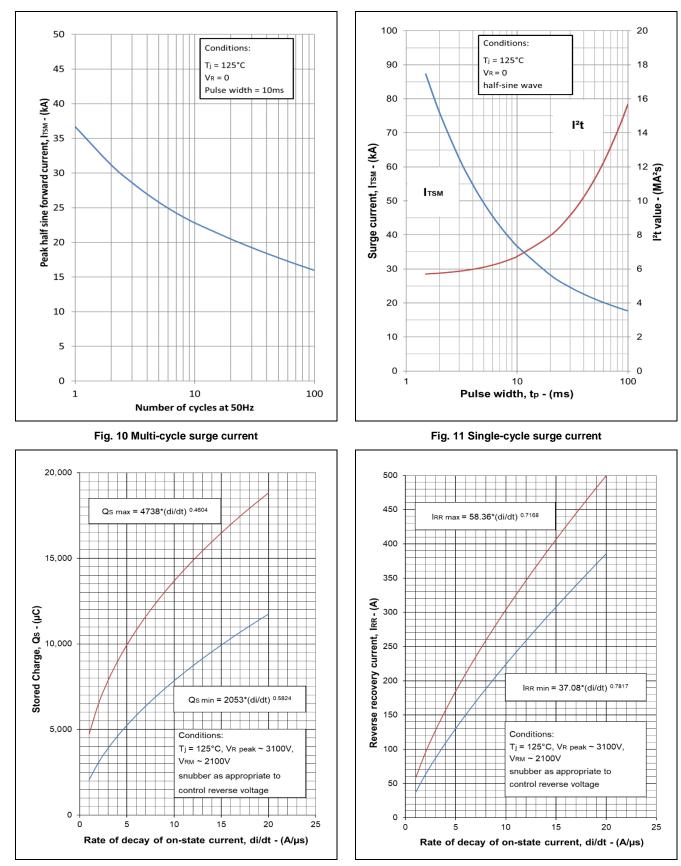
 $\Delta R_{th(j-c)}$  Conduction

Tables show the increments of thermal resistance R  $_{\text{frij-ej}}$  when the device operates at conduction angles other than d.c.

	Double side cooling		Anode Side Cooling		Cooling	Ca	thode Side	d Cooling
	ΔZ <sub>th</sub>	(Z)		ΔZ	2th (Z)		ΔZ	н (Z)
θ°	sine.	rect.	θ°	sine.	rect.	θ°	sine.	rect.
180	1.34	0.88	180	1.34	0.88	180	1.33	0.88
120	1.57	1.30	120	1.57	1.30	120	1.57	1 29
90	1.83	1.54	90	1 84	1.54	90	183	1.53
60	2.08	1.81	60	2.08	1.81	60	2.07	1.80
30	2.27	2.11	30	2.28	2.11	30	2.26	2.10
15	2.36	2.28	15	2.37	2.28	15	2.35	2.26

Fig. 9 Maximum (limit) transient thermal impedance – junction to case (degC/kW)

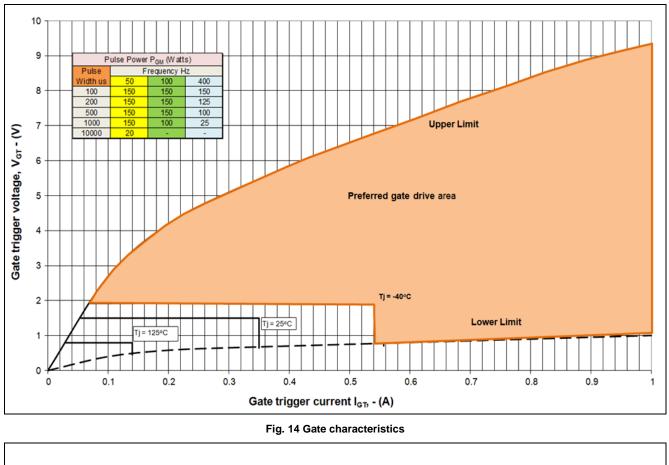
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Fig. 12 Stored charge

Fig. 13 Reverse recovery current



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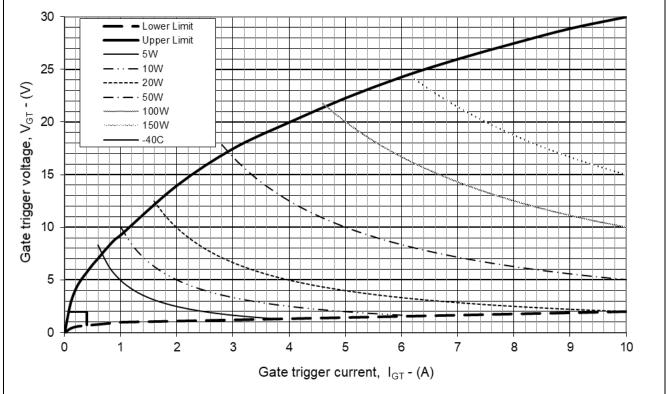


Fig. 15 Gate characteristics

## PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

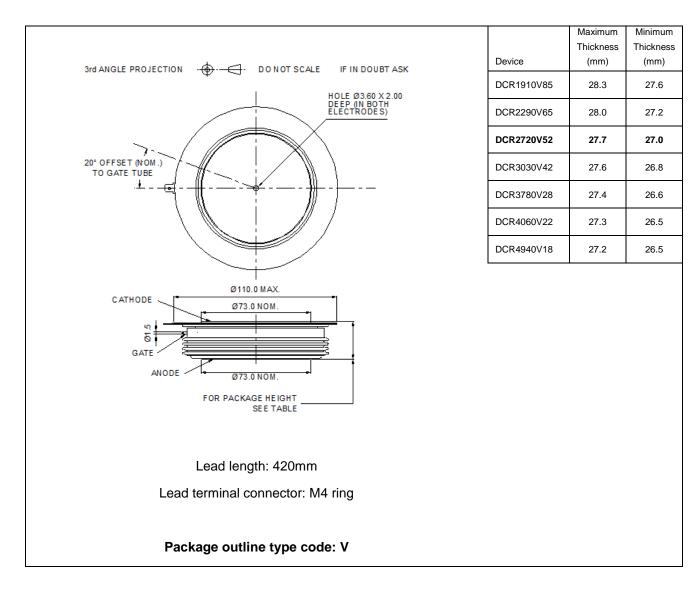


Fig. 16 Package outline

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